EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	195	shimada near yasushi.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:55
L2	52	hirata near yoshitaka.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:56
L3	22	kuriya near hiroyuki.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:56
L4	0	ptsuka near kazuhisa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:57
L5	198	otsuka near kazuhisa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:57
L6	421	yamaguchi near masanori.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:57
L7	29	shimayama near yuichi.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:58
L8	8	madarame near ken.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:58
L9	7	mizushima near etsuo.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:58

L10	6	kondou near yuusuke.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:59
L11	8	yamamoto near kazumori.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:59
L12	4706	(multilayer near wiring near board)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:00
L13	260	(multilayer near wiring near board) with (electrode$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:24
L14	52	(multilayer near wiring near board) with (electrode$1) with (capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:04
L15	2643	((high-dielectric) (high near dielectric)) with (electrode$1) with (capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:29
L16	79	15 and (wiring near3 board)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:23
L17	6	16 and (planariz$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:25
L18	25	16 and (through-hole$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:25
L19	431	((high-dielectric) (high near dielectric)) with (electrode$1) with (capacitor) with (conduct$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:35

L20	8	((high-dielectric) (high near dielectric)) with (electrode$1) with (capacitor) with (conduct$3) with (planariz$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:31
L21	115	((high-dielectric) (high near dielectric)) with (electrode$1) with (capacitor) with (conduct$3) and (planariz$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:31
L22	133	19 and (conduct$3) with (fill$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:38
L23	173	19 and (conduct$3) with (hole$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:39
L24	61	19 and (conduct$3) with (hole$1) with (fill$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:41
L25	24	24 and Planariz$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:51
L26	88955	(capacitor) with (arbitary layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:55
L27	15	(capacitor) with (arbitary layer) with (warpage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:57
L28	31274	(capacitor) with (capacity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:58
L29	5354	(capacitor) with (capacity) with (electrode$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:58

L30	77	(capacitor) with (capacity) with (electrode$1) with (counter near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:01
L31	1	(capacitor) with (capacity) with (electrode$1) with (counter near electrode) with (thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:59
L32	0	(capacitor) with (inductiv$3 near3 capacity) with (electrode$1) with (counter near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:02
L33	0	(capacitor) with (inductiv$3 near3 capacity) with (counter near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:02
L34	136	(capacitor) with (inductiv$3 near3 capacity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:02
L35	26	(capacitor) with (inductiv$3 near3 capacity) with (electrode$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:04
L36	792	(dielectric near material) with (fill$3) with (hole$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:04
L37	57	(dielectric near material) with (fill$3) with (hole$1) with (conduct$3 near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:10
L38	320	(dielectric near material) with (fill$3) with (hole$1) with (conduct$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:10
L39	34	38 and (capacitor) with (electrode$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:20

L40	2	"6707685".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:21
L41	324	(((multilayer) (multi-layer)) near wiring near board) with (electrode$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:24
L42	66	(((multilayer) (multi-layer)) near wiring near board) with (electrode$1) with (capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:29
L43	41	(((multilayer) (multi-layer)) near wiring near board) with (electrode$1) with (capacitor) with (dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:29
L44	167	((wiring near board) with (electrode$1)) with (capacitor) with (dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:30
L45	167	(wiring near board) with (electrode$1) with (capacitor) with (dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:42
L46	76	"5162977" "6265090"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:43